

IN THE CLAIMS:

On the first page of the claims, first line, change "What is claimed is:" to:

--What Is Claimed Is:--.

Please cancel original claims 1 to 18, without prejudice, and cancel substitute claims 1 to 19, without prejudice, in the underlying PCT Application No. PCT/EP00/06772.

Please add the following new claims:

Part 1.08

¹⁹ 20. (New) A reflectometer comprising:
a silicon substrate;
first subsections disposed on the substrate, each of the first subsections having etched oblique surfaces, the surfaces positioned to that light beams directed incident to the surfaces cause no retroreflection; and
Second subsections having relatively higher reflecting properties as compared to the first subsections;
wherein first subsections and second subsections are alternatively disposed on the substrate in a first direction.

²⁰ 21. (New) The reflectometer as recited in claim 1, wherein the oblique surfaces comprise a plurality of adjacent V-shaped grooves, the grooves disposed in a second direction perpendicular to the first direction, each of the grooves having a first surface and a second surface.

²¹ 22. (New) The reflectometer as recited in claim 2, wherein the grooves are regularly spaced in the first subsections.

²² 23. (New) The reflectometer as recited in claim 2, wherein the first surface and the second surface of each of the grooves are oriented at an angle of approximately 72° to one another.

²³ 24. (New) The reflectometer as recited in claim 1, wherein the silicon substrate

is monocrystalline silicon, and wherein the first direction corresponds to a direction of the monocrystalline silicon.

~~24~~ 25. (New) The reflectometer as recited in claim 1, wherein a width in the first direction of each of the first subsections is equivalent to a width in the first direction of each of the second subsections.

~~25~~ 26. (New) The reflectometer as recited in claim 2, wherein each of the first subsections further comprises at least one secondary V-shaped groove that extends in the second direction along nearly an entire length of an edge of each of the first subsections.

~~26~~ 27. (New) The reflectometer as recited in claim 1, wherein a coating of highly reflective material is applied to the second subsections.

~~27~~ 28. (New) The reflectometer as recited in claim 1, wherein the oblique surfaces form pyramid-shaped depressions.

~~28~~ 29. (New) The reflectometer as recited in claim 1, wherein the oblique surfaces are positioned so that a light beams directed thereon from a direction of incidence will reflect from the oblique surfaces in a direction that coincides with a direction other than the direction of incidence.

~~29~~ 30. (New) A method for manufacturing a reflectometer comprising the steps of:

- providing a silicon substrate;
- forming first subsections and second subsections that alternatively extend in a first direction on the silicon substrate, the first subsections and the second subsections having different optical reflecting properties;
- wherein, in the first subsections, a plurality of oblique surfaces is produced by deep etching, the oblique surfaces positioned such that no retroreflection of the light beams incident thereto results.

~~30~~ 31. (New) The method as recited in claim 11 further comprising the step of:

forming a plurality of V-shaped grooves in a second direction perpendicular to the first direction.

~~31~~ ³² (New) The method as recited in claim 12, wherein the forming step includes selectively etching oblique surfaces into the silicon substrate using an etching solution, in a region of the first subsections.

~~32~~ ³³ (New) The method as recited in claim 13 further comprising a step, prior to the forming step, of:

covering at least the second subsections with an etching mask on the silicon surface.

~~33~~ ³⁴ (New) The method as recited in claim 14, wherein the etching mask is formed from chromium.

~~34~~ ³⁵ (New) The method as recited in claim 13, wherein the etching solution is formed from potassium hydroxide in combination with isopropanol.

~~35~~ ³⁶ (New) The method as recited in claim 13, wherein the etching process continues until each of the V-shaped grooves is completely formed.

~~36~~ ³⁷ (New) The method as recited in claim 14, further comprising the step of: removing the etching mask after completion of the forming step.

~~37~~ ³⁸ (New) The method as recited in claim 11, wherein a plurality of pyramid-shaped depressions is etched into the silicon substrate in the first subsections.

Remarks

This Preliminary Amendment cancels original claims 1-18, without prejudice, and also cancels substitute claims 1 to 19, without prejudice, in the underlying